

1N662 • 1N662A • 1N663 • 1N663A

GENERAL PURPOSE DIFFUSED SILICON PLANAR* DIODES

• BV ... 100 V (MIN) @ 100 μ A

ABSOLUTE MAXIMUM RATINGS (Note 1)

Maximum Temperatures

Storage Temperature -65°C to +200°C
 Operating Junction Temperature 175°C

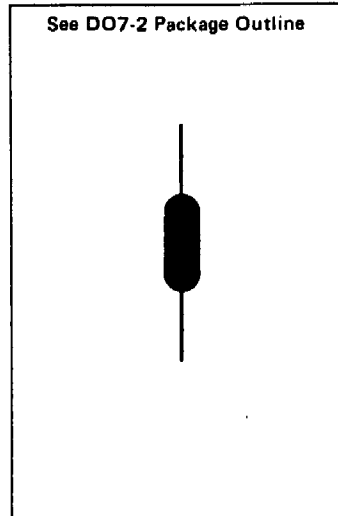
Maximum Power Dissipation (Notes 2 & 3)

Total Dissipation at 25°C Ambient Temperature 400 mW
 Linear Derating Factor 2.67 mW/°C

Maximum Voltage and Currents

WIV Working Inverse Voltage 80 V
 I_O Average Rectified Current 175 mA
 I_F Forward Current Steady State 400 mA
 i_f(surge) Peak Forward Surge Current 500 mA
 Pulse Width = 1.0 s 4.0 A
 Pulse Width = 1.0 μ s

See DO7-2 Package Outline



ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	1N662		1N662A		UNITS	TEST CONDITIONS
		MIN.	MAX.	MIN.	MAX.		
V _F	Forward Voltage		1.0		1.0	V	I _F = 10 mA
I _R	Reverse Current		1.0		1.0	μ A	I _F = 100 mA
			20		20	μ A	V _R = 10 V
			20		20	μ A	V _R = 10 V, T _A = 100°C
			100		100	μ A	V _R = 50 V
BV	Breakdown Voltage	100		100		V	V _R = 50 V, T _A = 100°C
t _{rr}	Reverse Recovery Time		500		300	ns	I _R = 100 μ A V _r = 40 V, I _f = 5.0 mA, R _L = 2.3 k Ω , C _L = 40 pF, Recovery to 100 k Ω

SYMBOL	CHARACTERISTIC	1N663		1N663A		UNITS	TEST CONDITIONS
		MIN.	MAX.	MIN.	MAX.		
V _F	Forward Voltage		1.0		1.0	V	I _F = 100 mA
I _R	Reverse Current		5.0		1.0	μ A	V _R = 75 V
			50		15	μ A	V _R = 75 V, T _A = 100°C
BV	Breakdown Voltage	100		100		V	I _R = 100 μ A
t _{rr}	Reverse Recovery Time		500		300	ns	V _r = 40 V, I _f = 5.0 mA, R _L = 2.3 k Ω , C _L = 40 pF, Recovery to 200 k Ω